TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

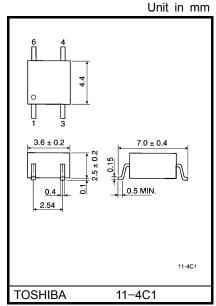
TLP124

Office Machine
Programmable Controllers
AC / DC-Input Module
Telecommunication

The TOSHIBA mini flat coupler TLP124 is a small outline coupler, suitable for surface mount assembly.

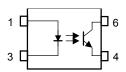
TLP124 consists of a photo transistor optically coupled to a gallium arsenide infrared emitting diode.

- Collector-emitter voltage: 80 V min.
- Current transfer ratio: 100% min. Rank BV: 200% min.
- Isolation voltage: 3750Vrms min.
- UL recognized: UL1577, file No. E67349



Weight: 0.09g

Pin Configurations (top view)



- 1 : Anode
- 3 : Cathode
- 4 : Emitter
- 6 : Collector

Current Transfer Ratio

Classification	Curr			
	Ta = 25°C		Ta = -25~75°C	Marking Of
	$I_F = 1mA$ $I_F = 0.5mA$		I _F = 1mA	Classification
	$V_{CE} = 0.5V$	V _{CE} = 1.5V	$V_{CE} = 0.5V$	
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV, Blank

(Note) Application type name for certification test, please use standard product type name, i. e. TLP124 (BV): TLP124

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	lF	50	mA
	Forward current derating	ΔI _F / °C	–0.7 (Ta ≥ 53°C)	mA / °C
LED	Peak forward current (100µs pulse, 100pps)	I _{FP}	1	Α
	Reverse voltage	V _R	5	V
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	V _{CEO}	80	٧
	Emitter-collector voltage	V _{ECO}	7	V
	Collector current	IC	50	mA
Detector	Peak collector current (10ms pulse, 100pps)	I _{CP}	100	mA
ă	Power dissipation	PC	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _C / °C	-1.5	mA / °C
	Junction temperature	Tj	125	°C
Sto	rage temperature range	T _{stg}	-55~125	°C
Оре	erating temperature range	T _{opr}	−55~100	°C
Lea	d soldering temperature (10s)	T _{sol}	260	°C
Tota	al package power dissipation	P _T	200	mW
	al package power dissipation ating (Ta ≥ 25°C)	ΔP _T / °C	-2.0	mW / °C
	ation voltage , 1min., R.H. ≤ 60%) (Note 1)	BV_S	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins1, 3 shorted together and pins 4, 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	48	V
Forward current	lF	_	1.6	20	mA
Collector current	IC	_	1	10	mA
Operating temperature	T _{opr}	-25	-	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I _R	V _R = 5 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	80	-	ı	٧
Detector	Emitter-collector breakdown voltage	V _(BR) ECO	I _E = 0.1 mA	7	-	ı	٧
Dete	Collector dark current	I _D	V _{CE} = 48 V	_	10	100	nA
	Collector dark current	טי	V _{CE} = 48 V, Ta = 85°C	_	2	50	μΑ
	Capacitance collector to emitter	C _{CE}	V = 0, f = 1 MHz	_	12	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	1 /1	I _F = 1mA, V _{CE} = 0.5 V	100	_	1200	%
Current transfer fatto	I _C / I _F	Rank BV	200	_	1200	70
Low input CTR	I _C / I _{F (low)}	I _F = 0.5 mA, V _{CE} = 1.5 V Rank BV	50	_	_	%
			100	_	_	70
	VCE (sat)	I _C = 0.5 mA, I _F = 1 mA	_	_	0.4	
Collector–emitter saturation voltage		I _C = 1 mA, I _F = 1 mA Rank BV	_	0.2	_	V
			_	_	0.4	
Off-state collector current	I _{C(off)}	V _F = 0.7V, V _{CE} = 48 V	_	_	10	μΑ

Coupled Electrical Characteristics (Ta = $-25\sim75^{\circ}$ C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	I _C / I _F	I _F = 1mA, V _{CE} = 0.5 V Rank BV	50	_	_	%
			100	_	_	%
Low input CTR	IC / IF (low)	I _F = 0.5 mA, V _{CE} = 1.5 V Rank BV	-	50	_	%
			_	100	_	%

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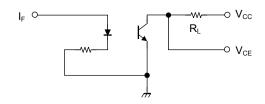
Isolation Characteristics (Ta = 25°C)

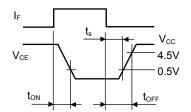
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	3750	_	_	V
		AC, 1 s, in oil	_	10000	_	V _{rms}
		DC, 1 minute, in oil	_	10000	_	V _{dc}

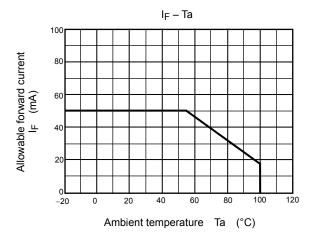
Switching Characteristics (Ta = 25°C)

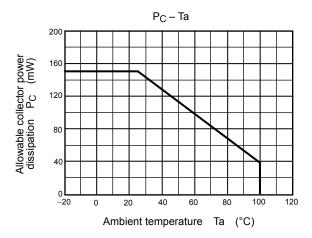
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t _r	V_{CC} = 10 V, I_C = 2 mA R_L = 100 Ω	_	8	_	
Fall time	t _f		_	8	_	116
Turn-on time	t _{ON}		_	10	_	μs
Turn-off time	toff		_	8	_	
Turn-on time	t _{ON}		_	10	_	
Storage time	ts	$R_L = 4.7 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = 1.6 \text{ mA}$	_	50	_	μs
Turn-off time	toff		_	300	-	

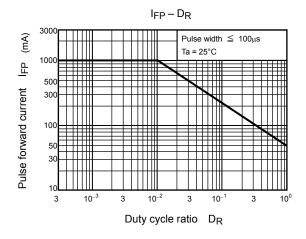
Fig. 1 Switching time test circuit

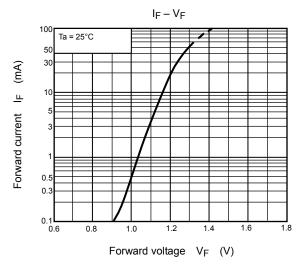


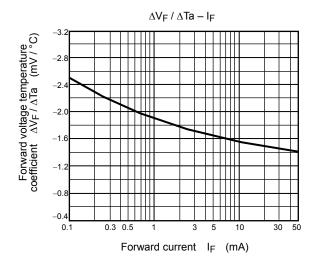


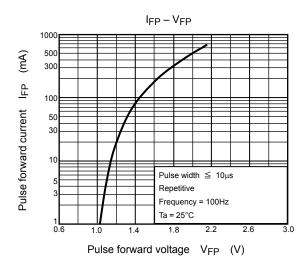




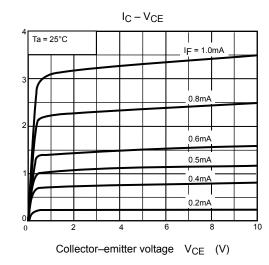




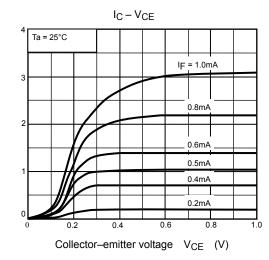




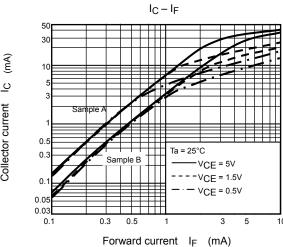
Collector current I_C (mA)

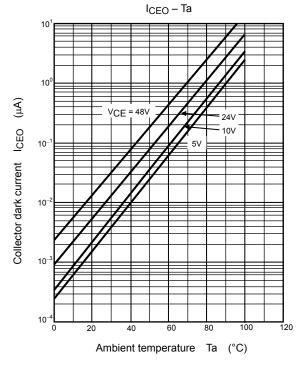


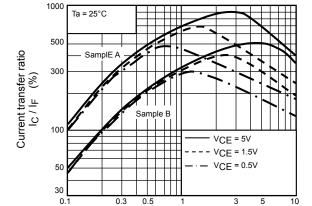
Collector current I_C (mA)



Collector current IC (mA)



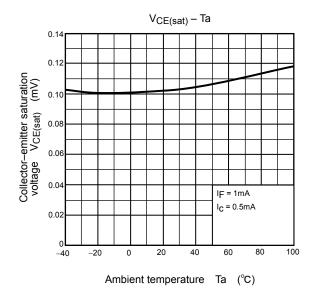


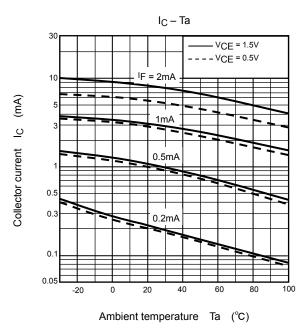


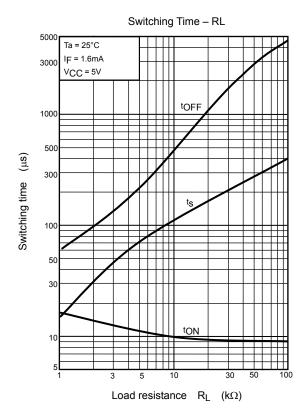
I_C / I_F – I_F

Forward current I_F (mA)

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